

DOCUMENT CHANGE REQUEST

515 DCR number Changes required for: General Originator: S Jeffery - ESCC Date: 2009/05/06 Organisation: ESA/ESTEC Date sent: 2009/05/06 Status: IMPLEMENTED Title: Transistors Low Power NPN, based on type 2N2857 Number: 2 5201/014 Issue: Other documents affected: Page: See attachment Paragraph: See attachment Original wording: Proposed wording: Update the Maximum Ratings table (see the attachment for details) so that this detail spec is clear, complete and the content and format is in-line with other detail specifications for similar Part Types. Justification: Improve the content and clarity of the spec. Attachments: 5201014_Issue_3_-_Draft_A.pdf, null Modifications: N/A Approval signature: 12. (c f(ai-4 Date signed: 2009-05-06

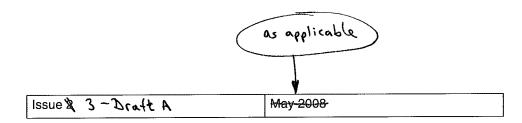


Pages 1 to 12

TRANSISTORS, LOW POWER, NPN

BASED ON TYPE 2N2857

ESCC Detail Specification No. 5201/014







ESCC Detail Specification No. 5201/014

PAGE 2

ISSUE & 3-Draft A

as applicable

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ESCC Detail Specification No. 5201/014

PAGE 3

ISSUE & 3 - Draft A

DOCUMENTATION CHANGE NOTICE

(Refer to https://escies.org for ESCC DCR content)

♥ SaSS¥ Spec	ification up issued to incorporate editorial and technical changes per DCR.
1 \	



ESCC Detail Specification No. 5201/014

PAGE 6

ISSUE & 3 - Draft A

Characteristics	Symbols	Maximum Ratings	Unit	Remarks	
Collector-Base Voltage	V _{CBO}	30	٧	Over entire operating temperature	
Collector-Emitter Voltage	V _{CEO}	15	٧		
Emitter-Base Voltage	V _{EBO}	2.5	٧	range	
Collector Current	I _C	40	mA	Continuous	
Power Dissipation	P _{tot} 1	200	mW	At T _{amb} ≤ +25°C	
·	Protz	300	mW	Aleteri.	
Operating Temperature Range	T _{op}	-55 to +175	°C		
Storage Temperature Range	T _{stg}	-65 to +200	°C		
Soldering Temperature	T _{sol}	+235	°C	Note 및 1	

NOTES:

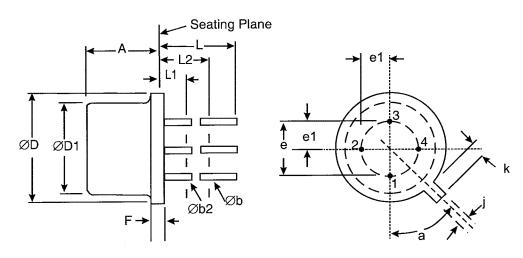
attached

1. For T_{amb} > ±25°C, derate linearly to 0W at +175°C.

2. Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.

PHYSICAL DIMENSIONS AND TERMINAL IDENTIFICATION 1.6

Metal Can Package (TO-72) - 4 lead 1.6.1



Symbols	Dimensio	Notes	
Symbols	Min	Max	Notes
Α	4.32	5.33	
Øb	0.406	0.533	2, 3
Øb2	0.406	0.483	2, 3
ØD	5.31	5.84	
ØD1	4.52	4.95	
е	2.54	TP	5

Thermal Resistance,				
Junction-to-Ambient	R _{th(j-a)}	750	°C/W	
Thermal Resistance,				
Junction-to-Case	R _{th(j-c)}	500	°C/W	